











TLV61220

ZHCS918A -MAY 2012-REVISED DECEMBER 2014

TLV61220 采用薄型 SOT-23 封装的低输入电压升压转换器

特性

- 在典型工作条件下效率高达 95%
- 5.5µA 静态电流
- 负载的启动输入电压为 0.7V
- 运行输入电压范围为 0.7V 至 5.5V
- 停机期间具有导通功能
- 最小开关电流为 200mA
- 保护特性:
 - 输出过压
 - 过热
 - 输入欠压闭锁
- 可调节输出电压范围为 1.8V 至 5.5V
- 小型 6 引脚超薄小外形尺寸晶体管 (SOT)-23 封装

2 应用范围

- 电池供电类 应用
 - 1至3节碱性电池、镍镉电池 (NiCd) 或者镍氢 电池 (NiMH)
 - 1 节锂离子或者锂离子一次性电池
- 太阳能或燃料电池供电 应用
- 消费类及便携式医疗产品
- 个人护理产品
- 白色或者状态发光二极管 (LED)
- 智能电话

典型应用电路原理图

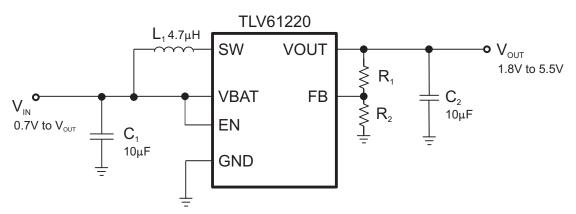
3 说明

TLV61220 器件可以为由单节、2 节或 3 节碱性、镍镉 或镍氢电池或单节锂离子或锂聚合物电池供电的产品提 供电源解决方案。可实现的输出电流取决于输入输出电 压比。升压转换器建立在采用同步整流的磁滞控制器拓 扑基础之上, 能够以最少的静态电流实现最高的效率。 可通过一个外部电阻分压器对此可调版本的输出电压进 行设定,或者可将此电压内部设定为一个固定值。此转 换器可由一个特定的使能引脚关闭。关闭时,电池消耗 降至最低。此器件采用一个 6 引脚超薄 SOT-23 封装 (DBV)。

器件信息(1)

器件型号	封装	封装尺寸(标称值)
TLV61220	SOT (6)	2.90mm x 1.60mm

(1) 如需了解所有可用封装,请见数据表末尾的可订购产品附录。





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5 修订历史记录

Changes from Original (May 2012) to Revision A

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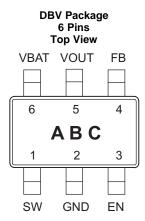
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6 Device Options

T _A	OUTPUT VOLTAGE DC/DC	PACKAGE	PART NUMBER
-40°C to 85°C	Adjustable	6-Pin SOT-23	TLV61220DBV

7 Pin Configuration and Functions



Pin Functions

PIN		I/O	DESCRIPTION				
NAME	NO.	1/0	DESCRIPTION				
EN	3	I	Enable input (VBAT enabled, GND disabled)				
FB	4	I	/oltage feedback for programming the output voltage				
GND	2	_	IC ground connection for logic and power				
SW	1	I	Boost and rectifying switch input				
VBAT	6	I	Supply voltage				
VOUT	5	0	Boost converter output				



8 Specifications

8.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) (1)

		MII	N MAX	UNIT
V _{IN}	Input voltage on VBAT, SW, VOUT, EN, FB	-0.	3 7.5	V
T_J	Operating junction temperature	-4	0 150	°C
T _{stg}	Storage temperature	-6	5 150	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

8.2 ESD Ratings

			VALUE	UNIT
		Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 (1)	±2000	ı
$V_{(ESD)}$	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1500	V

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

8.3 Recommended Operating Conditions

		MIN	NOM MAX	UNIT
V_{IN}	Supply voltage at VIN	0.7	5.5	V
T _A	Operating free air temperature range	-40	85	°C
T_{J}	Operating virtual junction temperature range	-40	125	°C

8.4 Thermal Information

	THERMAL METRIC ⁽¹⁾	DBV	UNIT
		6 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	185.7	
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	124.3	
$R_{\theta JB}$	Junction-to-board thermal resistance	31.3	°C/W
ΨЈТ	Junction-to-top characterization parameter	22.9	C/VV
ΨЈВ	Junction-to-board characterization parameter	30.8	
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	

⁽¹⁾ For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.



8.5 Electrical Characteristics

over recommended free-air temperature range and over recommended input voltage range (typical at an ambient temperature range of 25°C) (unless otherwise noted)

	PARAMETER	?	TEST CONDITIONS	MIN	TYP	MAX	UNIT
DC/DC ST	TAGE						
V _{IN}	Input voltage rar	nge		0.7		5.5	V
V _{IN}	Minimum input voltage at startup		R _{Load} ≥ 150 Ω			0.7	V
V _{OUT}	TLV61220 outpu	ıt voltage range	V _{IN} < V _{OUT}	1.8		5.5	V
V _{FB}	TLV61220 feedb	pack voltage		483	500	513	mV
I _{LH}	Inductor current	ripple			200		mA
			V _{OUT} = 3.3 V, V _{IN} = 1.2 V, T _A = 25 °C	220	400		mA
I_{SW}	switch current lin	mit	V _{OUT} = 3.3 V, T _A = -40°C to 85 °C	180	400		mA
			V _{OUT} = 3.3 V, T _A = 0°C to 85 °C	200	400		mA
	Rectifying switch	n on resistance.	V _{OUT} = 3.3 V		1000		mΩ
R _{DS(on)}	HSD	,	V _{OUT} = 5 V		700		mΩ
	NA-in audiah an		V _{OUT} = 3.3 V		600		mΩ
	Main switch on resistance, LSD		V _{OUT} = 5 V		550		mΩ
	Line regulation		V _{IN} < V _{OUT}		0.5%		
	Load regulation		V _{IN} < V _{OUT}		0.5%		
	Quiescent current	V _{IN}	1 0 7 1 1 1 0 1 1		0.5	0.9	μΑ
IQ		V _{OUT}	$I_{O} = 0 \text{ mA}, V_{EN} = V_{IN} = 1.2 \text{ V}, V_{OUT} = 3.3 \text{ V}$		5	7.5	μΑ
I _{SD}	Shutdown current	V _{IN}	V _{EN} = 0 V, V _{IN} = 1.2 V, V _{OUT} ≥ V _{IN}		0.2	0.5	μΑ
	Leakage current	into VOUT	V _{EN} = 0 V, V _{IN} = 1.2 V, V _{OUT} = 3.3 V		1		μΑ
I_{LKG}	Leakage current	into SW	$V_{EN} = 0 \text{ V}, V_{IN} = 1.2 \text{ V}, V_{SW} = 1.2 \text{ V}, V_{OUT} \ge V_{IN}$		0.01	0.2	μΑ
I _{FB}	TLV61220 Feed current	back input	V _{FB} = 0.5 V		0.01		μΑ
I _{EN}	EN input current		Clamped on GND or V _{IN} (V _{IN} < 1.5 V)		0.005	0.1	μΑ
CONTRO	L STAGE						
V _{IL}	EN input low vol	tage	V _{IN} ≤ 1.5 V			0.2 × V _{IN}	V
V _{IH}	EN input high vo	oltage	V _{IN} ≤ 1.5 V	0.8 × V _{IN}			V
V _{IL}	EN input low voltage		5 V > V _{IN} > 1.5 V			0.4	V
V _{IH}	EN input high voltage		5 V > V _{IN} > 1.5 V	1.2			V
V _{UVLO}	Undervoltage lo	ckout threshold	V _{IN} decreasing		0.5	0.7	٧
	Overvoltage pro	tection threshold		5.5		7.5	V
	Overtemperature	e protection			140		°C
	Overtemperature				20		°C



8.6 Typical Characteristics

Table 1. Table of Graphs

		FIGURE
	Input Voltage, I _{SW} = 330 mA, Minimum I _{SW} = 200 mA, V _O = 1.8V	Figure 1
Output Current	Input Voltage, I_{SW} = 400 mA, Minimum I_{SW} = 200 mA, V_O = 3.3V	Figure 2
	Input Voltage, $I_{SW} = 380$ mA, Minimum $I_{SW} = 200$ mA, $V_O = 5V$	Figure 3
	vs Output Current, $V_0 = 1.8 \text{ V}$, $V_1 = [0.7 \text{ V}; 1.2 \text{ V}; 1.5 \text{ V}]$	Figure 4
Efficiency	vs Output Current, $V_0 = 3.3 \text{ V}$, $V_1 = [0.7 \text{ V}; 1.2 \text{ V}; 2.4 \text{V}; 3 \text{V}]$	Figure 5
	vs Output Current, $V_0 = 5 \text{ V}$, $V_1 = [0.7 \text{ V}; 1.2 \text{ V}; 3.6 \text{V}; 4.2 \text{V}]$	Figure 6
	vs Input Voltage, $V_0 = 1.8 \text{ V}$, $I_0 = [100 \mu\text{A}; 1 \text{mA}; 10 \text{mA}; 50 \text{mA}]$	Figure 7
Efficiency	vs Input Voltage, $V_O = 3.3 \text{ V}$, $I_O = [100\mu\text{A}; 1\text{mA}; 10\text{mA}; 50\text{mA}]$	Figure 8
	vs Input Voltage, $V_0 = 5 \text{ V}$, $I_0 = [100\mu\text{A}; 1\text{mA}; 10\text{mA}; 50\text{mA}]$	Figure 9
0	vs Output Current, V _O = 1.8 V, V _I = [0.7 V; 1.2 V]	Figure 10
Output Voltage	vs Output Current, $V_0 = 3.3 \text{ V}$, $V_1 = [0.7 \text{ V}; 1.2 \text{ V}; 2.4 \text{ V}]$	Figure 11

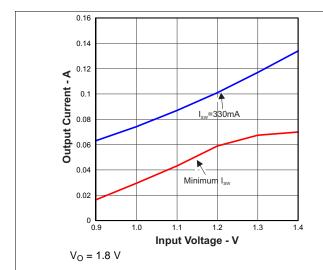
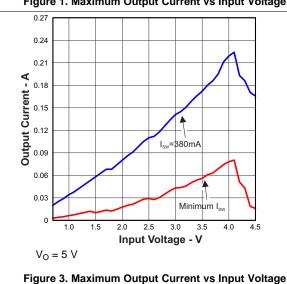


Figure 1. Maximum Output Current vs Input Voltage



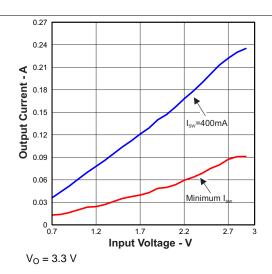


Figure 2. Maximum Output Current vs Input Voltage

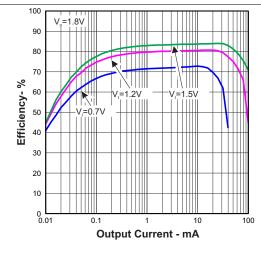
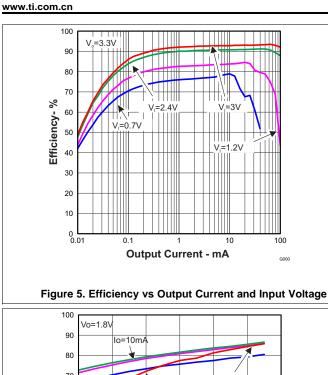


Figure 4. Efficiency vs Output Current and Input Voltage





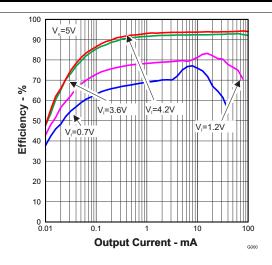
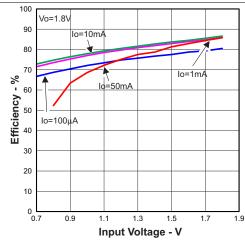


Figure 6. Efficiency vs Input Voltage and Output Current



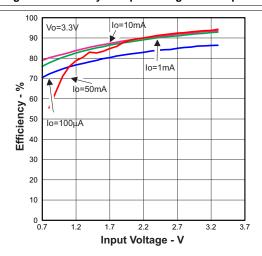


Figure 7. Efficiency vs Input Voltage and Output Current

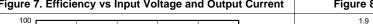
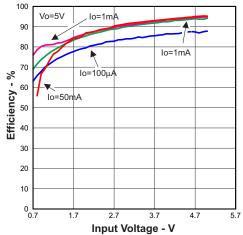


Figure 8. Efficiency vs Input Voltage and Output Current =1.8V



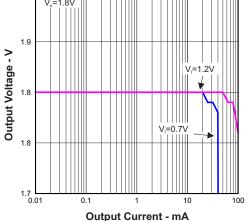
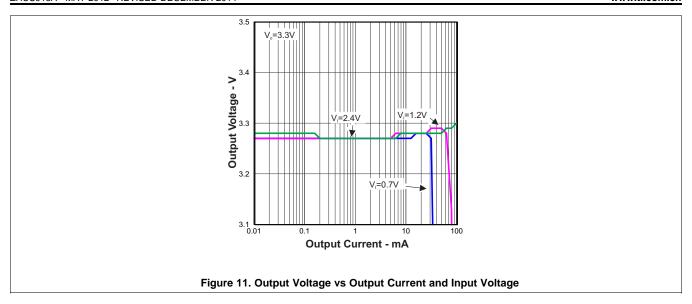


Figure 9. Efficiency vs Input Voltage and Output Current

Figure 10. Output Voltage vs Output Current and Input Voltage







9 Parameter Measurement Information

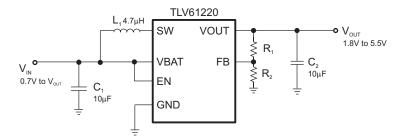


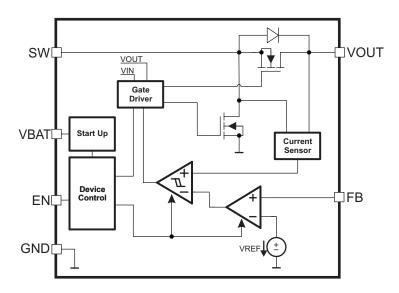
Figure 12. Parameter Measurement Schematic

10 Detailed Description

10.1 Overview

The TLV61220 is a high performance, highly efficient boost converter. To achieve high efficiency the power stage is realized as a synchronous boost topology. For the power switching two actively controlled low $R_{DS(on)}$ power MOSFETs are implemented.

10.2 Functional Block Diagram



10.3 Feature Description

10.3.1 Controller Circuit

The device is controlled by a hysteretic current mode controller. This controller regulates the output voltage by keeping the inductor ripple current constant in the range of 200 mA and adjusting the offset of this inductor current depending on the output load. In case the required average input current is lower than the average inductor current defined by this constant ripple the inductor current gets discontinuous to keep the efficiency high at low load conditions.

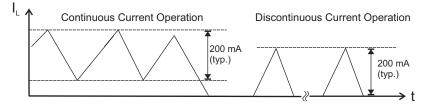


Figure 13. Hysteretic Current Operation

The output voltage V_{OUT} is monitored via the feedback network which is connected to the voltage error amplifier. To regulate the output voltage, the voltage error amplifier compares this feedback voltage to the internal voltage reference and adjusts the required offset of the inductor current accordingly. An external resistor divider needs to be connected.

The self oscillating hysteretic current mode architecture is inherently stable and allows fast response to load variations. It also allows using inductors and capacitors over a wide value range.



Feature Description (continued)

10.3.1.1 Startup

After the EN pin is tied high, the device starts to operate. In case the input voltage is not high enough to supply the control circuit properly a startup oscillator starts to operate the switches. During this phase the switching frequency is controlled by the oscillator and the maximum switch current is limited. As soon as the device has built up the output voltage to about 1.8 V, high enough for supplying the control circuit, the device switches to its normal hysteretic current mode operation. The startup time depends on input voltage and load current.

10.3.1.2 Operation at Output Overload

If in normal boost operation the inductor current reaches the internal switch current limit threshold the main switch is turned off to stop further increase of the input current.

In this case the output voltage will decrease since the device can not provide sufficient power to maintain the set output voltage.

If the output voltage drops below the input voltage the backgate diode of the rectifying switch gets forward biased and current starts flow through it. This diode cannot be turned off, so the current finally is only limited by the remaining DC resistances. As soon as the overload condition is removed, the converter resumes providing the set output voltage.

10.3.1.3 Undervoltage Lockout

An implemented undervoltage lockout function stops the operation of the converter if the input voltage drops below the typical undervoltage lockout threshold. This function is implemented in order to prevent malfunctioning of the converter.

10.3.1.4 Overvoltage Protection

If, for any reason, the output voltage is not fed back properly to the input of the voltage amplifier, control of the output voltage will not work anymore. Therefore an overvoltage protection is implemented to avoid the output voltage exceeding critical values for the device and possibly for the system it is supplying. For this protection the TLV61220 output voltage is also monitored internally. In case it reaches the internally programmed threshold of 6.5 V typically the voltage amplifier regulates the output voltage to this value.

If the TLV61220 is used to drive LEDs, this feature protects the circuit if the LED fails.

10.3.1.5 Overtemperature Protection

The device has a built-in temperature sensor which monitors the internal IC junction temperature. If the temperature exceeds the programmed threshold (see electrical characteristics table), the device stops operating. As soon as the IC temperature has decreased below the programmed threshold, it starts operating again. To prevent unstable operation close to the region of overtemperature threshold, a built-in hysteresis is implemented.

10.4 Device Functional Modes

10.4.1 Device Enable and Shutdown Mode

The device is enabled when EN is set high and shut down when EN is low. During shutdown, the converter stops switching and all internal control circuitry is turned off. In this case the input voltage is connected to the output through the back-gate diode of the rectifying MOSFET. This means that there always will be voltage at the output which can be as high as the input voltage or lower depending on the load.



11 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

11.1 Application Information

The TLV61220 is intended for systems powered by a single cell battery to up to three Alkaline, NiCd or NiMH cells with a typical terminal voltage between 0.7 V and 5.5 V. It can also be used in systems powered by one-cell Li-lon or Li-Polymer batteries with a typical voltage between 2.5 V and 4.2 V. Additionally, any other voltage source with a typical output voltage between 0.7 V and 5.5 V can be used with the TLV61220.

11.2 Typical Application

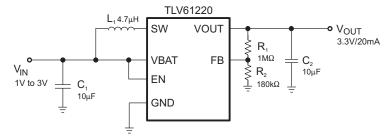


Figure 14. Typical Application Circuit for Adjustable Output Voltage Option

11.2.1 Design Requirements

In this example, TLV61220 is used to design a 3.3-V power supply with up to 50-mA output current capability. The TLV61220 can be powered by a single-cell battery to up to three Alkaline, NiCd or NiMH cells with a typical terminal voltage between 0.7 V and 5.5 V. It can also be used in systems powered by one-cell Li-lon or Li-Polymer batteries with a typical voltage between 2.5 V and 4.2 V. In this example, the input voltage range is from 2 V to 3 V for one-cell coin cell battery input design.

Table 2. TLV61220 3.3 V Output Design Requirements

PARAMETERS	VALUES
Input Voltage	2 V to 3 V
Output Voltage	3.3 V
Output Current	50 mA

11.2.2 Detailed Design Procedure

Table 3. List of Components

		•	
COMPONENT REFERENCE	PART NUMBER	MANUFACTURER	VALUE
C ₁	GRM188R60J106ME84D	Murata	10 μF, 6.3V. X5R Ceramic
C ₂	GRM188R60J106ME84D	Murata	10 μF, 6.3V. X5R Ceramic
L ₁	1269AS-H-4ZR7N	Toko	4.7 μH
R ₁ , R ₂			R_1 = 1M Ω , R_2 = Values depending on the programmed output voltage



11.2.2.1 Adjustable Output Voltage Version

An external resistor divider is used to adjust the output voltage. The resistor divider needs to be connected between VOUT, FB and GND as shown in Figure 14. When the output voltage is regulated properly, the typical voltage value at the FB pin is 500 mV. The maximum recommended value for the output voltage is 5.5 V. The current through the resistive divider should be about 100 times greater than the current into the FB pin. The typical current into the FB pin is 0.01 μ A, and the voltage across the resistor between FB and GND, R₂, is typically 500 mV. Based on those two values, the recommended value for R₂ should be lower than 500 kΩ, in order to set the divider current to 1 μ A or higher. The value of the resistor connected between VOUT and FB, R₁, depending on the needed output voltage (V_{OUT}), can be calculated using Equation 1:

$$R_1 = R_2 \times \left(\frac{V_{OUT}}{V_{FB}} - 1 \right) \tag{1}$$

As an example, if an output voltage of 3.3 V is needed, a 1-M Ω resistor is calculated for R₁ when for R₂ a 180-k Ω has been selected.

11.2.2.2 Inductor Selection

To make sure that the TLV61220 can operate, a suitable inductor must be connected between pin VBAT and pin SW. Inductor values of $4.7~\mu H$ show good performance over the whole input and output voltage range .

Choosing other inductance values affects the switching frequency f proportional to 1/L as shown in Equation 2.

$$L = \frac{1}{f \times 200 \text{ mA}} \times \frac{V_{IN} \times (V_{OUT} - V_{IN})}{V_{OUT}}$$
(2)

Choosing inductor values higher than 4.7 μ H can improve efficiency due to reduced switching frequency and, therefore, with reduced switching losses. Using inductor values below 2.2 μ H is not recommended.

Having selected an inductance value, the peak current for the inductor in steady state operation can be calculated. Equation 3 gives the peak current estimate.

$$I_{L,MAX} = \begin{cases} \frac{V_{OUT} \times I_{OUT}}{0.8 \times V_{IN}} + 100 \text{ mA}; & \text{continous current operation} \\ 200 \text{ mA}; & \text{discontinuous current operation} \end{cases}$$
(3)

For selecting the inductor this would be the suitable value for the current rating. It also needs to be taken into account that load transients and error conditions may cause higher inductor currents.

Equation 4 helps to estimate whether the device will work in continuous or discontinuous operation depending on the operating points. As long as the inequation is true, continuous operation is typically established. If the inequation becomes false, discontinuous operation is typically established.

$$\frac{V_{\text{OUT}} \times I_{\text{OUT}}}{V_{\text{IN}}} > 0.8 \times 100 \text{ mA}$$
(4)

The following inductor series from different suppliers have been used with TLV61220 converters:

Table 4. List of Inductors

VENDOR	INDUCTOR SERIES			
Toko	DFE252010C			
Coilcraft	EPL3015			
Concrait	EPL2010			
Murata	LQH3NP			
Taiyo Yuden	NR3015			
Wurth Elektronik	WE-TPC Typ S			



11.2.2.3 Capacitor Selection

11.2.2.3.1 Input Capacitor

At least a 10- μ F input capacitor is recommended to improve transient behavior of the regulator and EMI behavior of the total power supply circuit. A ceramic capacitor placed as close as possible to the VBAT and GND pins of the IC is recommended.

11.2.2.3.2 Output Capacitor

For the output capacitor C_2 , it is recommended to use small ceramic capacitors placed as close as possible to the VOUT and GND pins of the IC. If, for any reason, the application requires the use of large capacitors which can not be placed close to the IC, the use of a small ceramic capacitor with an capacitance value of around $2.2\mu F$ in parallel to the large one is recommended. This small capacitor should be placed as close as possible to the VOUT and GND pins of the IC.

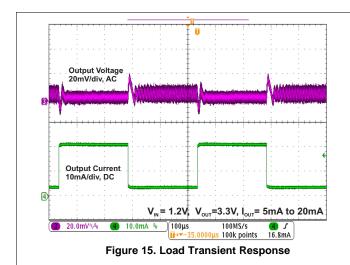
A minimum capacitance value of 4.7 μ F should be used, 10 μ F are recommended. If the inductor value exceeds 4.7 μ H, the value of the output capacitance value needs to be half the inductance value or higher for stability reasons, see Equation 5.

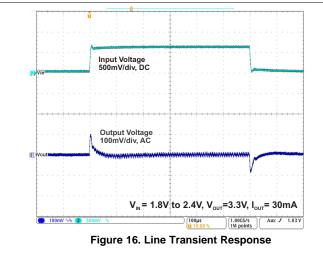
$$C_2 \ge \frac{L}{2} \times \frac{\mu F}{\mu H} \tag{5}$$

The TLV61220 is not sensitive to the ESR in terms of stability. Using low ESR capacitors, such as ceramic capacitors, is recommended anyway to minimize output voltage ripple. If heavy load changes are expected, the output capacitor value should be increased to avoid output voltage drops during fast load transients.

11.2.3 Application Curves

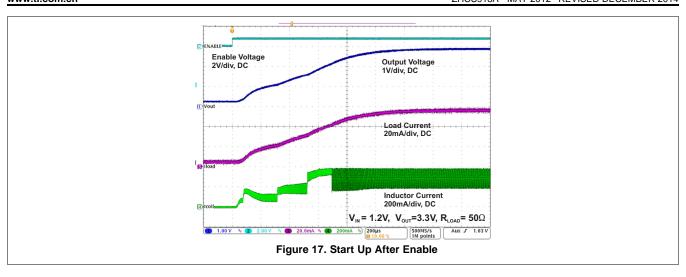
	FIGURE
Load transient, $V_I = 1.2 \text{ V}$, $V_O = 3.3 \text{ V}$, $I_O = 5 \text{mA}$ to 20 mA	Figure 15
Line transient, V_I = 1.8 V to 2.4V, V_O = 3.3 V, I_O = 30 mA	Figure 16
Startup after Enable, V_I = 1.2 V, V_O = 3.3 V, R_{LOAD} = 50 Ω	Figure 17





14







12 Power Supply Recommendations

The power supply can be single-cell, two-cell, or three-cell alkaline, NiCd or NiMH, or one-cell Li-lon or Lipolymer battery.

The input supply should be well regulated with the rating of TLV61220. If the input supply is located more than a few inches from the device, additional bulk capacitance may be required in addition to the ceramic bypass capacitors. An electrolytic or tantalum capacitor with a value of 47 µF is a typical choice.

13 Layout

13.1 Layout Guidelines

As for all switching power supplies, the layout is an important step in the design, especially at high peak currents and high switching frequencies. If the layout is not carefully done, the regulator could show stability problems as well as EMI problems. Therefore, use wide and short traces for the main current path and for the power ground paths. The input and output capacitor, as well as the inductor should be placed as close as possible to the IC.

The feedback divider should be placed as close as possible to the control ground pin of the IC. To lay out the ground, it is recommended to use short traces as well, separated from the power ground traces. This avoids ground shift problems, which can occur due to superimposition of power ground current and control ground current. Assure that the ground traces are connected close to the device GND pin.

13.2 Layout Example

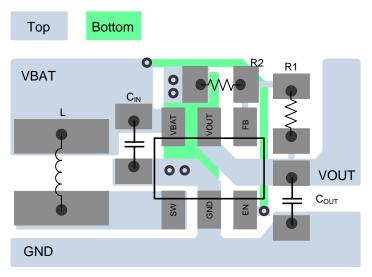


Figure 18. PCB Layout Recommendation

13.3 Thermal Considerations

Implementation of integrated circuits in low-profile and fine-pitch surface-mount packages typically requires special attention to power dissipation. Many system-dependent issues such as thermal coupling, airflow, added heat sinks and convection surfaces, and the presence of other heat-generating components affect the power-dissipation limits of a given component.

Three basic approaches for enhancing thermal performance are listed below.

- Improving the power-dissipation capability of the PCB design
- Improving the thermal coupling of the component to the PCB
- Introducing airflow in the system

For more details on how to use the thermal parameters in the dissipation ratings table please check the *Thermal Characteristics Application Note* (SZZA017) and the *IC Package Thermal Metrics Application Note* (SPRA953).



14 器件和文档支持

14.1 器件支持

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14.2 文档支持

14.2.1 相关文档

相关文档请参见以下部分:

- 《散热特性数据应用手册》, SZZA017
- 应用手册《IC 封装热指标》(文献编号: SPRA953)

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14.5 术语表

SLYZ022 — TI 术语表。

这份术语表列出并解释术语、首字母缩略词和定义。

15 机械、封装和可订购信息

以下页中包括机械、封装和可订购信息。这些信息是针对指定器件可提供的最新数据。这些数据会在无通知且不对本文档进行修订的情况下发生改变。欲获得该数据表的浏览器版本,请查阅左侧的导航栏。

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PACKAGE OPTION ADDENDUM

3-Aug-2016

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
TLV61220DBVR	ACTIVE	SOT-23	DBV	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	VUAI	Samples
TLV61220DBVT	ACTIVE	SOT-23	DBV	6	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	VUAI	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM

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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLV61220DBVR	SOT-23	DBV	6	3000	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
TLV61220DBVT	SOT-23	DBV	6	250	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3

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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLV61220DBVR	SOT-23	DBV	6	3000	180.0	180.0	18.0
TLV61220DBVT	SOT-23	DBV	6	250	180.0	180.0	18.0



SMALL OUTLINE TRANSISTOR



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.

- 4. Leads 1,2,3 may be wider than leads 4,5,6 for package orientation. 5. Refernce JEDEC MO-178.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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